

Amendments to the Specification

Replace [Para 0028] with:

For example, plasma etching of a copper-coated wafer 24 in the presence of chlorine gas results in the formation of a layer of copper chloride (CuCl_2) in the non-masked areas of wafer 24. Due to the partial pressure of CuCl_2 , the surface of wafer 24 will be passivated at temperatures below 600 ~~degree~~ degrees F and no etching will occur. Radiating with infrared radiation 36 at a resonance wavelength will effectively lower the temperature at which the layer of CuCl_2 formed on the area of wafer 24 ~~evaporated~~ will evaporate to form the etching. By contrast, the surrounding areas of wafer 36 that are masked to prevent the formation of CuCl_2 will be heated to a lesser degree as selected wavelength infrared radiation 30 will not induce resonance in those regions.